

IN THE CLAIMS

Claim 1 (Currently Amended): A method for measuring a dielectric constant of a thin film sample, comprising:

irradiating a sample with light at a first incident angle, whereby the light undergoes multiple internal reflections within the sample;

measuring light that has transmitted through or reflected on the sample following said multiple internal reflections; and

determining a complex dielectric constant of the sample ~~depending~~ based upon a spectrum of the transmitted or reflected light that has undergone said multiple internal reflections.

Claim 2 (Currently Amended): ~~[[A]]~~ The method according to claim 1, wherein a complex dielectric constant of the sample is determined by setting an incident angle of the incident light upon the sample at 60 degrees or greater and smaller than 90 degrees.

Claim 3 (Currently Amended): ~~[[A]]~~ The method according to claim 1 ~~[[or 2]]~~, wherein the sample is a substrate having a uniform dielectric constant and uniform thickness or ~~[[a]]~~ the sample having a thin film provided on a part of the substrate.

Claim 4 (Currently Amended): ~~[[A]]~~ The method according to ~~any of claims 1 to 3~~ claim 1, wherein the irradiation light is S-polarized light.

Claim 5 (Currently Amended): ~~[[A]] The method according to any of claims 1 to 4~~ claim
1, wherein the irradiation light has a wavelength in a region of a millimeter wave, a
sub-millimeter wave or a tera-hertz frequency range of light.

Claim 6 (Currently Amended): An apparatus for measuring a complex dielectric constant
of a thin film sample ~~which measures a dielectric constant of a sample~~ by irradiating the sample
with light, comprising:~~[[;]]~~

a light irradiating unit that irradiates the sample with light at a first incident angle,
whereby the light undergoes multiple internal reflections within the sample;

a measuring unit that measures light ~~that has~~ transmitted through or reflected upon the
sample following said multiple internal reflections; and

a determining unit that determines ~~determining~~ a complex dielectric constant of the
sample ~~depending~~ based upon a spectrum of the transmitted or reflected light that has undergone
said multiple internal reflections.

Claim 7 (Currently Amended): ~~[[A]] The~~ apparatus according to claim 6, wherein
incident light upon the sample is changeable in the position, and a photodetector for receiving the
transmitted or reflected light is also changeable in the position.

Claim 8 (Currently Amended): ~~[[A]] The~~ apparatus according to claim 6 ~~[[or 7]]~~,
wherein incident light upon the sample is changeable in incident angle.

Claim 9 (New): The apparatus according to claim 7, wherein incident light upon the sample is changeable in incident angle.

Claim 10 (New): The method according to claim 2, wherein the sample is a substrate having a uniform dielectric constant and uniform thickness or [[a]] the sample having a thin film provided on a part of the substrate.

Claim 11 (New): The method according to claim 2, wherein the irradiation light has a wavelength in a region of a millimeter wave, a sub-millimeter wave or a tera-hertz frequency range of light.

Claim 12 (New): The method according to claim 3, wherein the irradiation light has a wavelength in a region of a millimeter wave, a sub-millimeter wave or a tera-hertz frequency range of light.